## NSN 5961-00-495-7125

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Inclosure Material:
Metal
Overall Length:
1.204 inches
Mounting Facility Quantity:
1
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-64
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case and mounting hardware
Overall Width Across Flats:
Between 0.424 inches and 0.437 inches
Thread Size:
0.190 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
50.0 repetitive peak reverse voltage, peak total value and 75.0 nonrepetitive peak reverse voltage, peak total value and 2.0 gate trigge
voltage, dc
Current Rating Per Characteristic:
30.00 milliamperes forward current, total rms preset
Test Data Document:
00752-395548 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 2 tab, solder lug
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig: